National Semiconductor

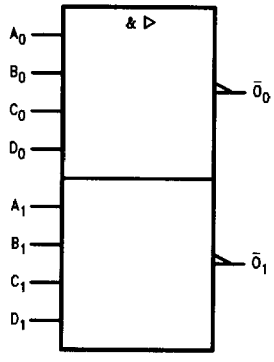
54F/74F40
Dual 4-Input NAND Buffer

General Description

This device contains two independent gates, each of which performs the logic NAND function.

Ordering Code: See Section 5

Logic Symbol



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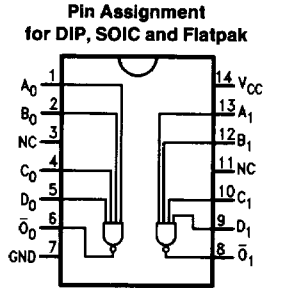
Connection Diagrams



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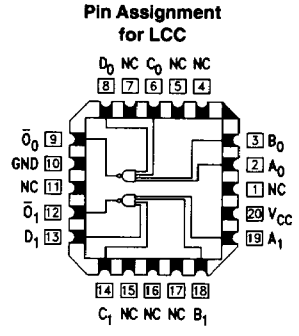

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Unit Loading/Fan Out: See Section 2 for U.L. definitions

Pin Names	Description	54F/74F	
		U.L. HIGH/LOW	Input I_{IH}/I_{IL} Output I_{OH}/I_{OL}
A_n, B_n, C_n, D_n	Inputs	1.0/2.0	20 μA/−1.2 mA
$\overline{O}_n$	Outputs	600/106.6 (80)	−12 mA/64 mA (48 mA)

Function Table

Inputs				Output
A	B	C	D	$\overline{O}$
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	−65°C to +150°C
Ambient Temperature under Bias	−55°C to +125°C
Junction Temperature under Bias	−55°C to +175°C
V_{CC} Pin Potential to Ground Pin	−0.5V to +7.0V
Input Voltage (Note 2)	−0.5V to +7.0V
Input Current (Note 2)	−30 mA to +5.0 mA
Voltage Applied to Output in HIGH State (with V_{CC} = 0V)	
Standard Output	−0.5V to V_{CC}
TRI-STATE® Output	−0.5V to +5.5V
Current Applied to Output in LOW State (Max)	twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	−55°C to +125°C
Commercial	0°C to +70°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F Min	54F/74F Typ	54F/74F Max	Units	V_{CC}	Conditions
V_{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V_{CD}	Input Clamp Diode Voltage				−1.2	V	Min	I_{IN} = −18 mA
V_{OH}	Output HIGH Voltage	54F 10% V_{CC}	2.4			V	Min	I_{OH} = −3 mA
		54F 10% V_{CC}	2.0					I_{OH} = −12 mA
		74F 10% V_{CC}	2.4					I_{OH} = −3 mA
		74F 10% V_{CC}	2.0					I_{OH} = −15 mA
		74F 5% V_{CC}	2.7					I_{OH} = −3 mA
V_{OL}	Output LOW Voltage	54F 10% V_{CC}			0.55	V	Min	I_{OL} = 48 mA
		74F 10% V_{CC}			0.55			I_{OL} = 64 mA
I_{IH}	Input HIGH Current	54F			20.0	μA	Max	V_{IN} = 2.7V
		74F			5.0			
I_{BVI}	Input HIGH Current Breakdown Test	54F			100	μA	Max	V_{IN} = 7.0V
		74F			7.0			
I_{CEX}	Output High Leakage Current	54F			250	μA	Max	V_{OUT} = V_{CC}
		74F			50			
V_{ID}	Input Leakage Test	74F	4.75			V	0.0	I_{ID} = 1.9 μA All Other Pins Grounded
I_{OD}	Output Leakage Circuit Current	74F			3.75	μA	0.0	V_{IOD} = 150 mV All Other Pins Grounded
I_{IL}	Input LOW Current				−1.2	mA	Max	V_{IN} = 0.5V
I_{OS}	Output Short-Circuit Current		−100		−225	mA	Max	V_{OUT} = 0V
I_{CCH}	Power Supply Current			1.6	4.0	mA	Max	V_O = HIGH
I_{CCL}	Power Supply Current			13.0	17.0	mA	Max	V_O = LOW

AC Electrical Characteristics: See Section 2 for Waveforms and Load Configurations

Symbol	Parameter	74F $T_A = +25°C$, $V_{CC} = +5.0V$, $C_L = 50$ pF			54F T_A, V_{CC} = Mil, $C_L = 50$ pF		74F T_A, V_{CC} = Com, $C_L = 50$ pF		Units	Fig. No.
		Min	Typ	Max	Min	Max	Min	Max		
t_{PLH}	Propagation Delay	2.0	3.0	6.0			1.5	7.0	ns	2-3
t_{PHL}	A_n, B_n, C_n, D_n to $\overline{O}_n$	1.5	2.5	5.0			1.0	5.5		